

IGBT Die

Features

- ## Typical Applications

- Industrial Motor Drives
- Solar Inverters
- UPS Systems
- Welding

Parameter	Symbol	Value	Unit
Collector–Emitter Voltage, $T_J = 25^{\circ}\text{C}$	V_{CE}	650	V
DC Collector Current, limited by $T_{J(\text{max})}$	I_C	(Note 1)	A
Pulsed Collector Current (Note 2)	$I_{C, \text{pulse}}$	120	A
Gate–Emitter Voltage	V_{GE}	± 20	V
Maximum Junction Temperature	T_J	-55 to $+175$	$^{\circ}\text{C}$
Short Circuit Withstand Time, $V_{GE} = 15 \text{ V}$, $V_{CE} = 400\text{V}$, $T_J \leq 150^{\circ}\text{C}$	T_{SC}	5.0	μs

2. T_{pulse} limited by T_{imax} , 5.0 μs pulse, $V_{\text{GE}} = 15 \text{ V}$.

Parameter	Value	Unit
Die Size	3550 x 3550	μm^2
Emitter Pad Size	See die layout	μm^2
Gate Pad Size	410 x 670	μm^2
Die Thickness	3	mils
Wafer Size	150	mm
Top Metal	4 μm AlSi	
Back Metal	2 μm TiNiAg	
Max possible chips per wafer	996	
Passivation frontside	Oxide-Nitride	
Reject ink dot size	25 mils	
Recommended storage environment: In original container, in dry nitrogen, or temperature of 18–28°C, 30–65%RH	Type: Die on tape in ring-pack Storage time: < 3 months	

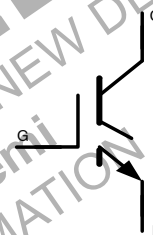
Device	Inking?	Shipping
NGTD13T65F2WP	Yes	Bare Wafer on Tape
NGTD13T65F2SWK	Yes	Sawn Wafer on Tape



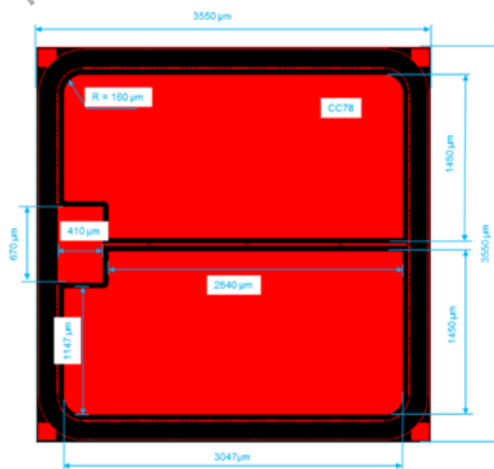
ON Semiconductor®

www.onsemi.com

$V_{RCE} = 650 \text{ V}$
 $I_C = \text{Limited by } T_{J(\text{max})}$



DIE OUTLINE



NGTD13T65F2

ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Units
-----------	-----------------	--------	-----	-----	-----	-------

STATIC CHARACTERISTICS

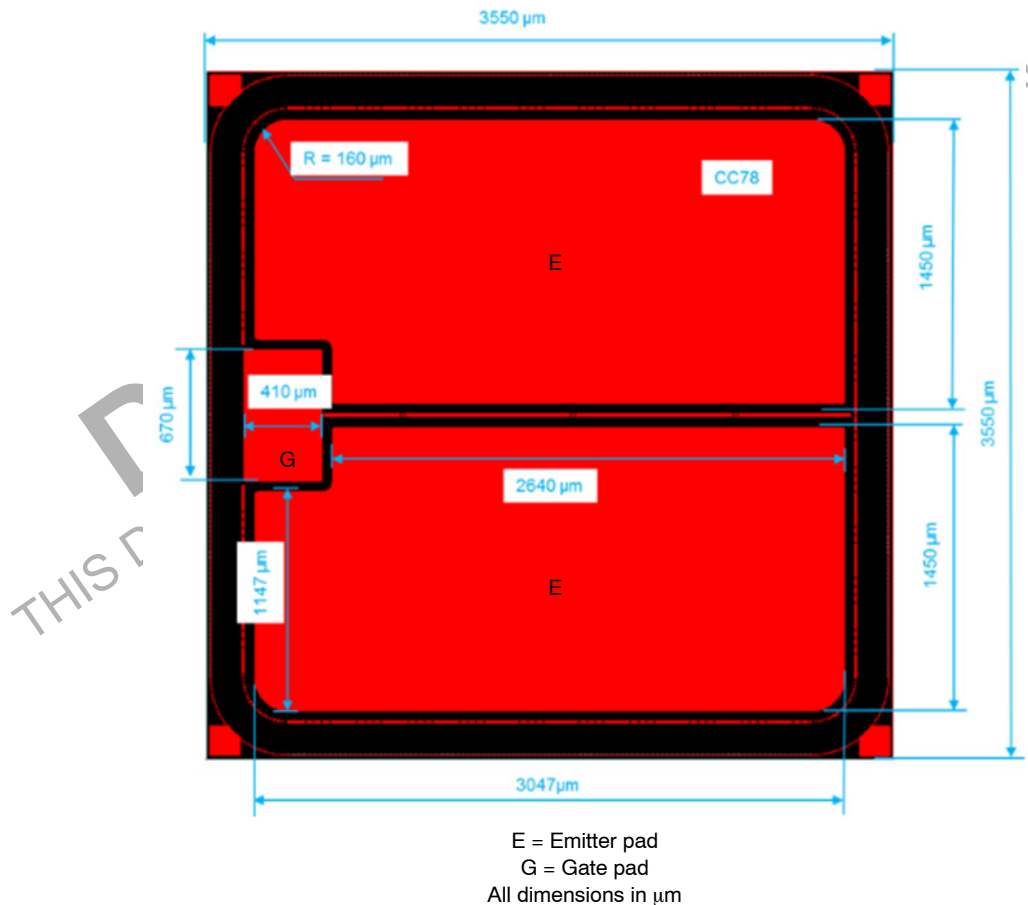
Collector–Emitter Breakdown Voltage	$V_{GE} = 0 \text{ V}, I_C = 500 \mu\text{A}$	$V_{(BR)CES}$	650			V
Collector–Emitter Saturation Voltage	$V_{GE} = 15 \text{ V}, I_C = 30 \text{ A}$	$V_{CE(sat)}$		1.6	2.2	V
Gate–Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 350 \mu\text{A}$	$V_{GE(TH)}$	4.5	5.5	6.5	V
Collector–Emitter Cutoff Current	$V_{GE} = 0 \text{ V}, V_{CE} = 650 \text{ V}$	I_{CES}			0.2	mA
Gate Leakage Current	$V_{GE} = 20 \text{ V}, V_{CE} = 0 \text{ V}$	I_{GES}			100	nA

DYNAMIC CHARACTERISTICS

Input Capacitance	$V_{CE} = 20 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$	C_{ies}		3200		pF
Output Capacitance		C_{oes}		130		pF
Reverse Transfer Capacitance		C_{res}		85		pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

DIE LAYOUT



Further Electrical Characteristic

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales